

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

SN75446, SN75447 DUAL PERIPHERAL DRIVERS

SLRS020A - DECEMBER 1978 - REVISED NOVEMBER 1995

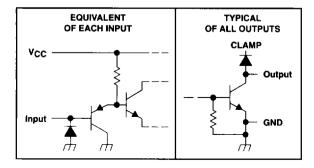
- Very Low Power Requirements
- Very Low Input Current
- Characterized for Use to 350 mA
- No Output Latch-Up at 50 V (After Conducting 300 mA)
- High-Voltage Outputs (70 V Min)
- Output Clamp Diodes for Transient Suppression (350 mA, 70 V)
- TTL- or MOS-Compatible Diode-Clamped Inputs
- Standard Supply Voltage
- Suitable for Hammer-Driver Applications

description

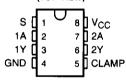
The SN75446 and SN75447 dual peripheral drivers are designed for use in systems that require high current, high voltage, and fast switching times. The SN75446 and SN75447 provide AND and NAND drivers, respectively. These devices have diode-clamped inputs as well as high-current, high-voltage inductive-clamp diodes on the outputs.

The SN75446 and SN75447 drivers are characterized for operation from 0°C to 70°C.

schematics of inputs and outputs



D OR P PACKAGE (TOP VIEW)



Function Tables

SN75446 (each AND driver)

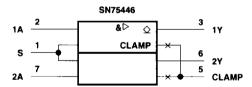
INPUTS		OUTPUT		
A	A S			
Н	н	Н		
L	X	L		
X	Ł	L		

SN75447 (each NAND driver)

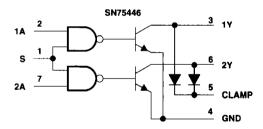
INPL	OUTPUT			
A S		Y		
Н	Н	L		
L.	Х	н		
X	L	н		

H = high level, L = low level X = irrelevant

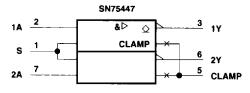
logic symbols†

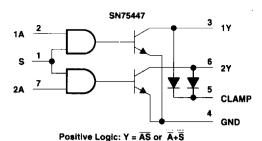


logic diagrams (positive logic)



Positive Logic: $Y = \overline{AS}$ or $\overline{A+S}$





[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage, V _{CC} (see Note 1)	7 V
Input voltage, V _I	5.5 V
Output current, IO (see Note 2)	400 mA
Output clamp-diode current	400 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Voltage values are with respect to network GND.

Both halves of this dual circuit may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation ratings.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW



SN75446, SN75447 **DUAL PERIPHERAL DRIVERS**

SLRS020A - DECEMBER 1978 - REVISED NOVEMBER 1995

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}	4.75	5	5.25	٧
High-level input voltage, VIH	2			٧
Low-level input voltage, V _{IL}			0.8	٧
Operating free-air temperature range, TA	0		70	[∞] C

electrical characteristics over recommended operating free-air temperature range

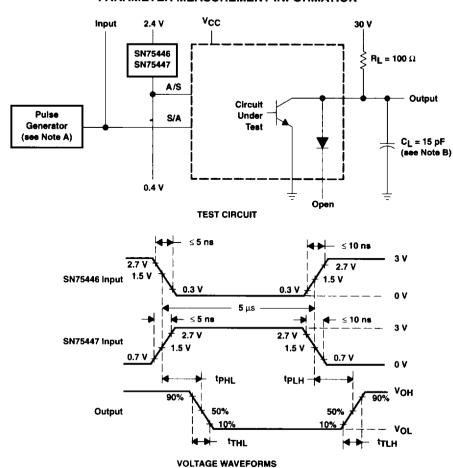
	PARAMETER		TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
ViK	Input clamp voltage		I _I = –12 mA			-0.9	-1.5	٧
	Low lovel output vallege			I _{OL} = 100 mA		0.1	0.3	٧
Voi			V _{CC} = 4.75 V, V _{1H} = 2 V,	I _{OL} = 200 mA		0.22	0.45	
VOL	Low-level output voltage	Low-level output voltage		I _{OL} = 300 mA		0.45	0.65	
			V _{IL} = 0.8 V	I _{OL} = 350 mA		0.55	0.75	
V _{O(BR)}	Output breakdown voltage		$V_{CC} = 4.75 \text{ V},$	I _{OH} = 100 μA	70	100		٧
V _{R(K)}	Output clamp-diode reverse vo	Itage	$V_{CC} = 4.75 \text{ V},$	I _R = 100 μA	70	100		٧
V _{F(K)}	Output clamp-diode forward voltage		$V_{CC} = 4.75 \text{ V},$	IF = 350 mA	0.6	1.2	1.6	٧
ф	High-level output current High-level input current		$V_{CC} = 4.75 \text{ V},$ $V_{IL} = 0.8 \text{ V},$	V _{IH} = 2 V, V _{OH} = 70 V		1	100	μΑ
ЧН			V _{CC} = 5.25 V,	V _j = 5.25 V		0.01	10	μА
1	Low level input overent	A input	V 505 V	V - 505 V V 00 V		-0.5	- 10	4
liL.	Low-level input current	S input	$V_{CC} = 5.25 \text{ V},$	$V_1 = 0.8 \text{ V}$		-1	-20	μA
1	Cupality acceptant acceptants high	SN75446	V 505 V	V ₁ = 5 V		11	18	A
CCH	Supply current, outputs high	SN75447	V _{CC} = 5.25 V	V _I = 0		11	18	mA
^I CCL	Supply current, outputs low	SN75446	V 5.05.V	V _I = 0		11	18	
		SN75447	V _{CC} = 5.25 V	V _I = 5 V	T	11	18	mA

[†] All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, $V_{CC} = 5$ V, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
[†] PLH	Propagation delay time, low-to-high-level output				300	750	ns
^t PHL	Propagation delay time, high-to-low-level output	C _L = 15 pF,	$R_L = 100 \Omega$,		200	500	ns
†TLH	Transition time, low-to-high-level output	See Figure 1	_		50	100	ns
[†] THL	Transition time, high-to-low-level output				50	100	ns
VOH	High-level output voltage after switching	V _S = 55 V, See Figure 2	$I_O \approx 300 \text{ mA},$	V _S -0.018			٧

PARAMETER MEASUREMENT INFORMATION

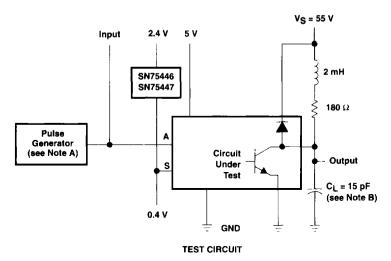


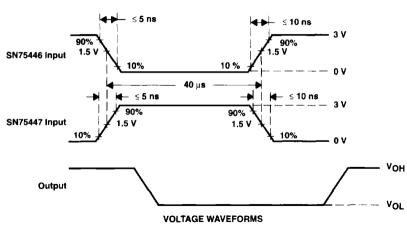
NOTES: A. The pulse generator has the following characteristics: PRR = 100 kHz, Z_O = 50 Ω .

B. C_L includes probe and jig capacitance.

Figure 1. Test Circuit and Voltage Waveforms, Switching Characteristics

PARAMETER MEASUREMENT INFORMATION





NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_O = 50 \Omega$.

B. C_L includes probe and jig capacitance.

Figure 2. Latch-Up Test Circuit and Voltage Waveforms